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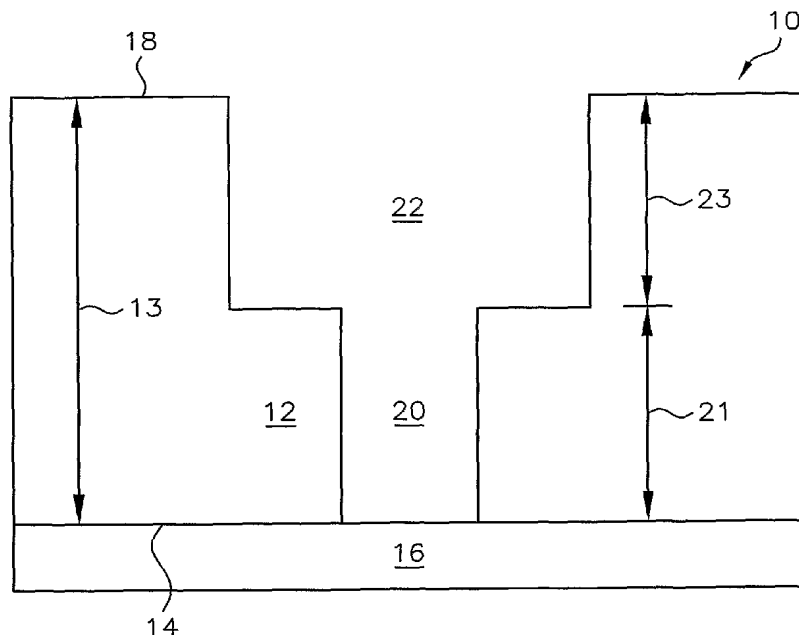
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(54) Title: GRADIENT DEPOSITION OF LOW-K CVD MATERIALS



(57) Abstract: A dielectric layer (12) for a semiconductor device having a low overall dielectric constant, good adhesion to the semiconductor substrate, and good resistance to cracking due to thermal cycling. The dielectric layer (12) is made by a process involving continuous variation of dielectric material deposition conditions to provide a dielectric layer having a gradient of dielectric constant.

WO 2005/071752 A1



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